Power MOSFET

72 A, 25 V, N-Channel DPAK

Features

- Planar HD3e Process for Fast Switching Performance
- Low R_{DS(on)} to Minimize Conduction Loss
- Low C_{ISS} to Minimize Driver Loss
- Low Gate Charge
- Pb-Free Packages are Available

MAXIMUM RATINGS (T_J = 25°C Unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V _{DSS}	25	V_{dc}
Gate-to-Source Voltage - Continuous	V _{GS}	±20	V_{dc}
Thermal Resistance – Junction-to-Case Total Power Dissipation @ T _C = 25°C Drain Current	$R_{ heta JC} P_D$	2.4 62.5	°C/W W
$ \begin{array}{lll} - \mbox{ Continuous } @\ T_C = 25^{\circ}\mbox{C}, \mbox{ Chip} \\ - \mbox{ Continuous } @\ T_C = 25^{\circ}\mbox{C}, \mbox{ Limited by Package} \\ - \mbox{ Continuous } @\ T_A = 25^{\circ}\mbox{C}, \mbox{ Limited by Wires} \\ - \mbox{ Single Pulse } (t_p = 10\ \mu\text{s}) \end{array} $	I _D I _D I _{DM}	72.0 62.8 32 140	A A A
Thermal Resistance – Junction-to-Ambient (Note1)	$R_{\theta JA}$	80	°C/W
Total Power Dissipation @ T _A = 25°C Drain Current - Continuous @ T _A = 25°C	P_{D}	1.87 12.0	W A
Thermal Resistance – Junction-to-Ambient (Note2)	$R_{\theta JA}$	110	°C/W
Total Power Dissipation @ T _A = 25°C Drain Current - Continuous @ T _A = 25°C	P_{D}	1.36 10.0	W A
Operating and Storage Temperature Range	T _J , T _{stg}	-55 to 175	°C
Single Pulse Drain-to-Source Avalanche Energy – Starting $T_J = 25^{\circ}C$ ($V_{DD} = 30 \ V_{dc}, \ V_{GS} = 10 \ V_{dc}, \ I_L = 12 \ A_{pk}, \ L = 1 \ mH, \ R_G = 25 \ \Omega)$	E _{AS}	71.7	mJ
Maximum Lead Temperature for Soldering Purposes, 1/8" from Case for 10 s	TL	260	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

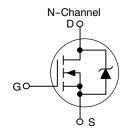
- 1. When surface mounted to an FR4 board using 0.5 sq. in. pad size.
- 2. When surface mounted to an FR4 board using minimum recommended pad size.



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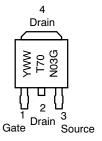
V _{(BR)DSS}	R _{DS(on)} TYP	I _D MAX
25 V	5.6 m Ω	72 A

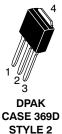


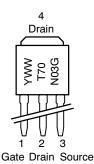
MARKING DIAGRAMS



CASE 369AA STYLE 2







70N03 = Device Code = Year WW = Work Week = Pb-Free Package

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

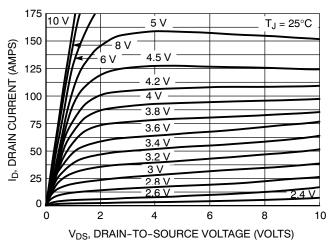
ELECTRICAL CHARACTERISTICS ($T_J = 25^{\circ}C$ Unless otherwise specified)

C	Symbol	Min	Тур	Max	Unit	
OFF CHARACTERISTICS					1	<u> </u>
Drain-to-Source Breakdown (V_{GS} = 0 V_{dc} , I_D = 250 μ A, Temperature Coefficient (Pos	V _{(br)DSS}	25 -	28 20.5	- -	V _{dc} mV/°C	
Zero Gate Voltage Drain Curr (V_{DS} = 20 V_{dc} , V_{GS} = 0 V_{cc}) (V_{DS} = 20 V_{dc} , V_{GS} = 0 V_{cc})	dc)	I _{DSS}	-	- -	1.5 10	μA _{dc}
Gate-Body Leakage Current $(V_{GS} = \pm 20 V_{dc}, V_{DS} = 0)$		I _{GSS}	-	-	±100	nA _{dc}
ON CHARACTERISTICS (No	ote 3)					
Gate Threshold Voltage (Note ($V_{DS} = V_{GS}$, $I_D = 250 \mu A_{d}$). Threshold Temperature Coeff	c) [']	V _{GS(th)}	1.0 -	1.5 4.0	2.0	V _{dc} mV/°C
Static Drain-to-Source On-F ($V_{GS} = 4.5 V_{dc}$, $I_D = 20 A_c$ ($V_{GS} = 10 V_{dc}$, $I_D = 20 A_d$	dc)	R _{DS(on)}	- -	8.1 5.6	13 8.0	mΩ
Forward Transconductance ($V_{DS} = 10 V_{dc}$, $I_D = 15 A_{dc}$	9FS	ı	27	-	Mhos	
DYNAMIC CHARACTERISTI	cs					
Input Capacitance		C _{ISS}	-	1333	-	pF
Output Capacitance	$(V_{DS} = 20 V_{dc}, V_{GS} = 0 V,$ f = 1 MHz)	C _{OSS}	-	600	-	
Transfer Capacitance	,	C _{RSS}	1	218	-	
SWITCHING CHARACTERIS	STICS (Note 4)					
Turn-On Delay Time		t _{d(on)}	-	6.9	-	ns
Rise Time	$(V_{GS} = 10 V_{dc}, V_{DD} = 10 V_{dc},$	t _r	-	1.3	-	
Turn-Off Delay Time	$I_D = 36 A_{dc}, R_G = 3 \Omega$	t _{d(off)}	-	18.4	-	
Fall Time]	t _f	-	5.5	-	
Gate Charge		Q _T	-	13.2	-	nC
	$(V_{GS} = 5 V_{dc}, I_D = 36 A_{dc}, V_{DS} = 10 V_{dc})$ (Note 3)	Q_{GS}	-	3.3	-	
	30, ()	Q_{DS}	-	6.5	-	
SOURCE-DRAIN DIODE CH	IARACTERISTICS					
Forward On-Voltage	$(I_S = 20 \text{ A}_{dc}, \text{ V}_{GS} = 0 \text{ V}_{dc}) \text{ (Note 3)}$ $(I_S = 20 \text{ A}_{dc}, \text{ V}_{GS} = 0 \text{ V}_{dc}, \text{ T}_J = 125^{\circ}\text{C})$	V _{SD}	- -	0.86 0.73	1.2	V _{dc}
Reverse Recovery Time	everse Recovery Time		-	27.9	-	ns
	(L 20 A V 2 V	t _a	-	14.8	-	7
	$(I_S = 36 A_{dc}, V_{GS} = 0 V_{dc}, dI_S/dt = 100 A/\mu s)$ (Note 3)	t _b	-	13.1	-	7
Reverse Recovery Stored Charge		Q _{RR}	1	19	-	nC

Pulse Test: Pulse Width = 300 μs, Duty Cycle = 2%.
 Switching characteristics are independent of operating junction temperatures.

TYPICAL PERFORMANCE CURVES ($T_J = 25^{\circ}C$ unless otherwise noted)

 $V_{DS} \geq 10 \; V$

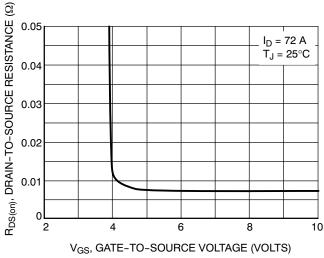


100 NBH 75 NJ = 25°C T_J = 25°C T_J = -55°C 0 2 4 6 8

Figure 1. On-Region Characteristics

V_{GS}, GATE-TO-SOURCE VOLTAGE (VOLTS)

Figure 2. Transfer Characteristics



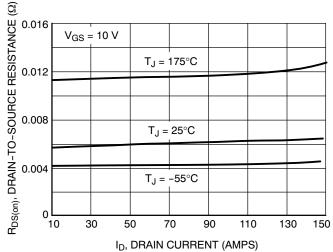
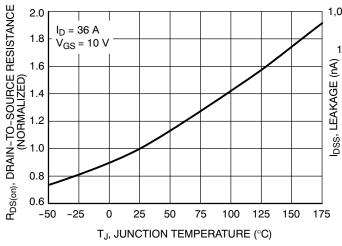


Figure 3. On-Resistance versus Gate-to-Source Voltage

Figure 4. On-Resistance versus Drain Current and Gate Voltage



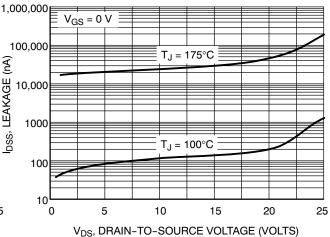
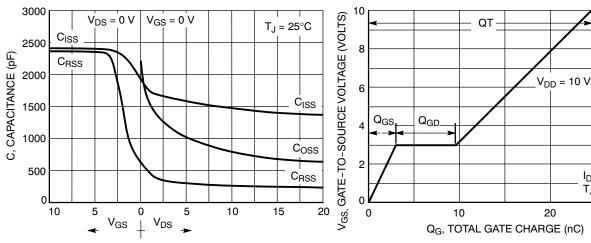


Figure 5. On-Resistance Variation with Temperature

Figure 6. Drain-to-Source Leakage Current versus Voltage



GATE-TO-SOURCE OR DRAIN-TO-SOURCE VOLTAGE (VOLTS)

Figure 7. Capacitance Variation

Figure 8. Gate-To-Source and Drain-To-Source Voltage versus Total Charge

 $I_D = 36 A$ $T_J = 25^{\circ}C$

30

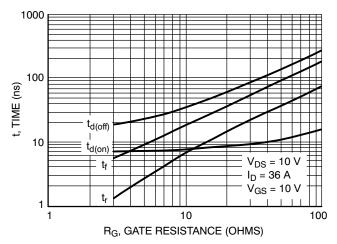


Figure 9. Resistive Switching Time Variation versus Gate Resistance

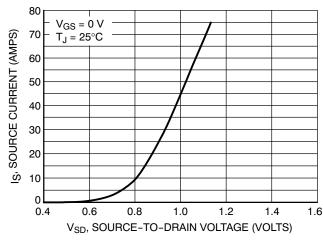


Figure 10. Diode Forward Voltage versus Current

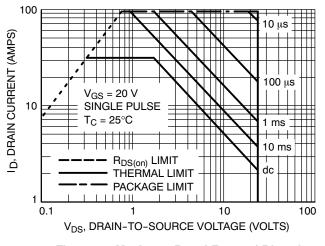


Figure 11. Maximum Rated Forward Biased Safe Operating Area

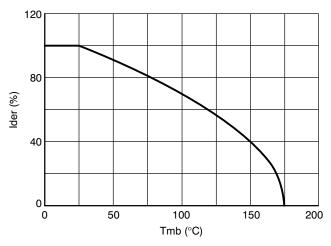


Figure 12. Normalized Continuous Drain Current as a function of Mounting Base Temperature

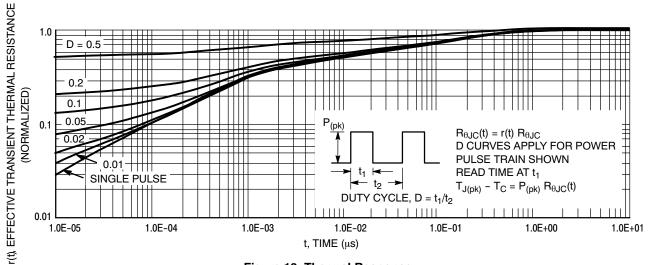


Figure 13. Thermal Response

ORDERING INFORMATION

Order Number	Package	Shipping †	
NTD70N03R	DPAK-3	75 Units / Rail	
NTD70N03RG	DPAK-3 (Pb-Free)	75 Units / Rail	
NTD70N03RT4	DPAK-3	2500 / Tape & Reel	
NTD70N03RT4G	DPAK-3 (Pb-Free)	2500 / Tape & Reel	
NTD70N03R-1	DPAK-3 Straight Lead	75 Units / Rail	
NTD70N03R-1G	DPAK-3 Straight Lead (Pb-Free)	75 Units / Rail	

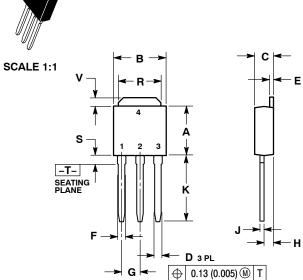
[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MECHANICAL CASE OUTLINE





DATE 15 DEC 2010



STYLE 2:

PIN 1. GATE

3

STYLE 6: PIN 1. MT1 2. MT2 3. GATE

2. DRAIN

4. DRAIN

MT2

SOURCE

STYLE 3: PIN 1. ANODE

2. CATHODE

4. CATHODE

3 ANODE

STYLE 7: PIN 1. GATE 2. COLLECTOR

3. EMITTER

COLLECTOR

STYLE 1: PIN 1. BASE

3

STYLE 5: PIN 1. GATE

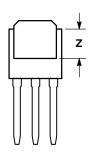
2. ANODE 3. CATHODE

ANODE

2. COLLECTOR

EMITTER

COLLECTOR



NOTES:

- DIMENSIONING AND TOLERANCING PER
- ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.

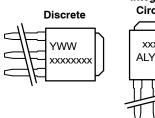
	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.235	0.245	5.97	6.35
В	0.250	0.265	6.35	6.73
С	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
Е	0.018	0.023	0.46	0.58
F	0.037	0.045	0.94	1.14
G	0.090	BSC	2.29	BSC
Н	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.350	0.380	8.89	9.65
R	0.180	0.215	4.45	5.45
S	0.025	0.040	0.63	1.01
٧	0.035	0.050	0.89	1.27
7	0.155		3 93	

MARKING DIAGRAMS

STYLE 4:
PIN 1. CATHODE
2. ANODE
3. GATE
4. ANODE

YWW

XXXXXXXXX





xxxxxxxx = Device Code
A = Assembly Location
IL = Wafer Lot
Y = Year
WW = Work Week

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STYLE 1: PIN 1. BASE

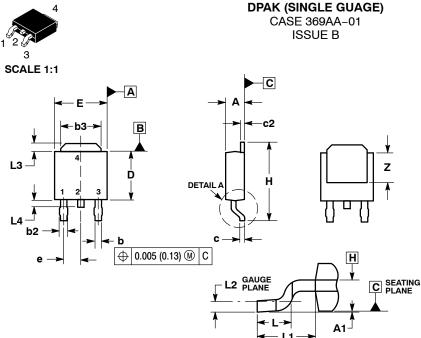
STYLE 5:

2. COLLECTOR 3. EMITTER

4. COLLECTOR

PIN 1. GATE 2. ANODE 3. CATHODE

4. ANODE



STYLE 3: PIN 1. ANODE

STYLE 7:

2. CATHODE 3. ANODE

PIN 1. GATE 2. COLLECTOR

3. EMITTER

COLLECTOR

CATHODE

DETAIL A ROTATED 90° CW

STYLE 4: PIN 1. CATHODE 2. ANODE 3. GATE



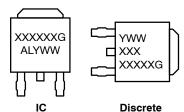
DATE 03 JUN 2010

NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- 2. CONTROLLING DIMENSION: INCHES.
 3. THERMAL PAD CONTOUR OPTIONAL WITHIN DI-MENSIONS b3, L3 and Z.
 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD
- FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE
- DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
- 6. DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.086	0.094	2.18	2.38
A1	0.000	0.005	0.00	0.13
b	0.025	0.035	0.63	0.89
b2	0.030	0.045	0.76	1.14
b3	0.180	0.215	4.57	5.46
С	0.018	0.024	0.46	0.61
c2	0.018	0.024	0.46	0.61
D	0.235	0.245	5.97	6.22
Е	0.250	0.265	6.35	6.73
е	0.090 BSC		2.29 BSC	
Н	0.370	0.410	9.40	10.41
L	0.055	0.070	1.40	1.78
L1	0.108 REF		2.74	REF
L2	0.020 BSC		0.51	BSC
L3	0.035	0.050	0.89	1.27
L4		0.040		1.01
Z	0.155		3.93	

GENERIC MARKING DIAGRAM*



XXXXXX = Device Code Α = Assembly Location L = Wafer Lot ٧ = Year = Work Week WW = Pb-Free Package

SOLDERING FOOTPRINT*

3. GATE

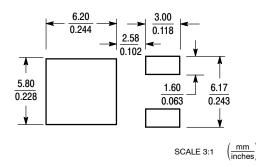
STYLE 2: PIN 1. GATE

STYLE 6:

PIN 1. MT1 2. MT2

2. DRAIN 3. SOURCE

4. DRAIN



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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^{*}This information is generic. Please refer to device data sheet for actual part marking.

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